



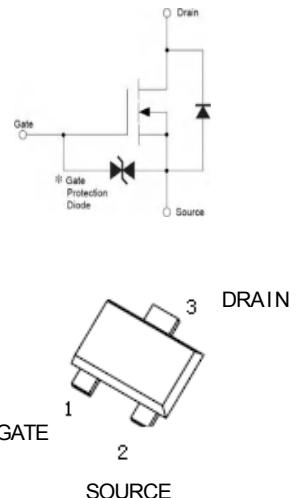
**迈拓电子**  
MAITUO ELECTRONIC

## 2SK3018M Plastic-Encapsulate MOSFETs

### FEATURES

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for portable equipment
- Easily designed drive circuits
- Easy to parallel

Marking: KN



### MOSFET MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	0.1	A
$P_D$	Power Dissipation	0.15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55~+150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C} / \text{W}$

SOT-723

### MOSFET ELECTRICAL CHARACTERISTICS( $T_a=25^\circ\text{C}$ unless otherwise noted)

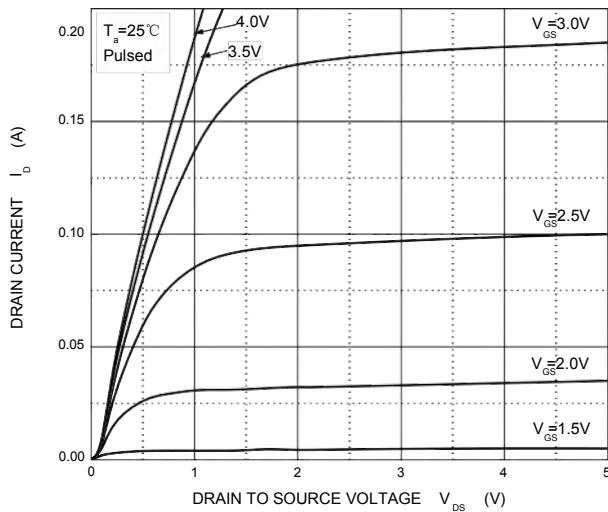
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0V, I_D = 10\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			0.2	$\mu\text{A}$
Gate –Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 2$	$\mu\text{A}$
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = 3V, I_D = 100\mu\text{A}$	0.8		1.5	V
Drain-Source On-Resistance	$R_{DS(\text{on})}$	$V_{GS} = 4V, I_D = 10\text{mA}$			8	$\Omega$
		$V_{GS} = 2.5V, I_D = 1\text{mA}$			13	$\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 3V, I_D = 10\text{mA}$	20			$\text{mS}$
<b>Dynamic Characteristics*</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{MHz}$		13		pF
Output Capacitance	$C_{oss}$			9		pF
Reverse Transfer Capacitance	$C_{rss}$			4		pF
<b>Switching Characteristics*</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 5V, V_{DD} = 5V, I_D = 10\text{mA}, R_g = 10\Omega, R_L = 500\Omega,$		15		ns
Rise Time	$t_r$			35		ns
Turn-Off Delay Time	$t_{d(off)}$			80		ns
Fall Time	$t_f$			80		ns



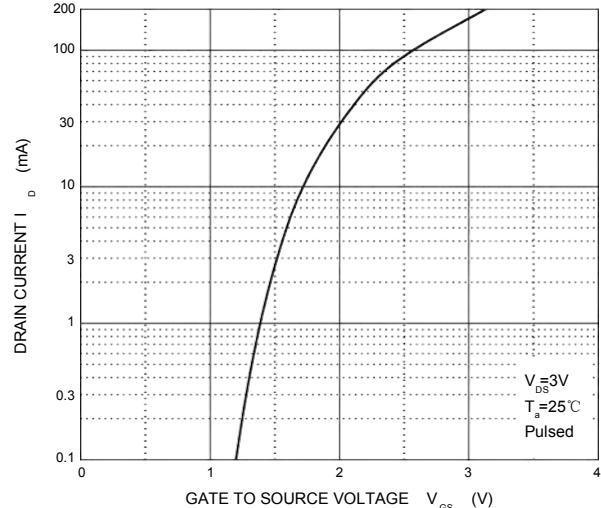
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## Typical Characteristics

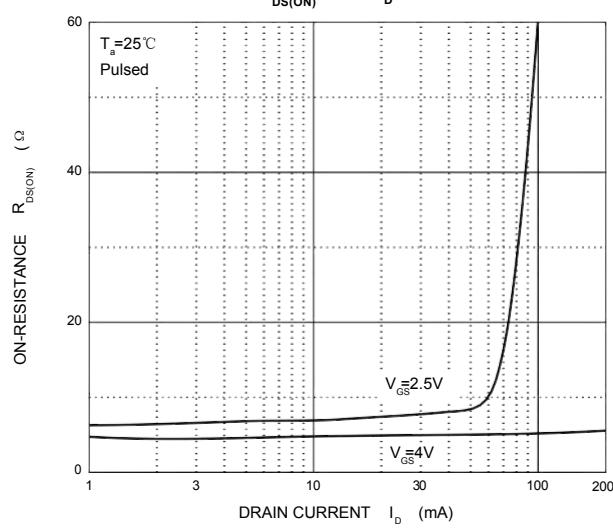
Output Characteristics



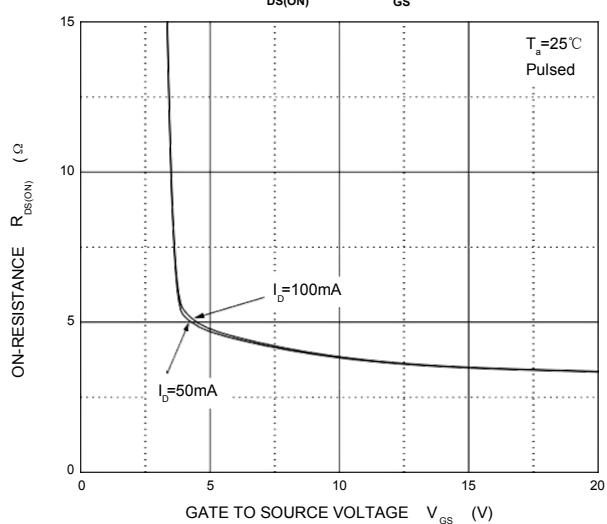
Transfer Characteristics



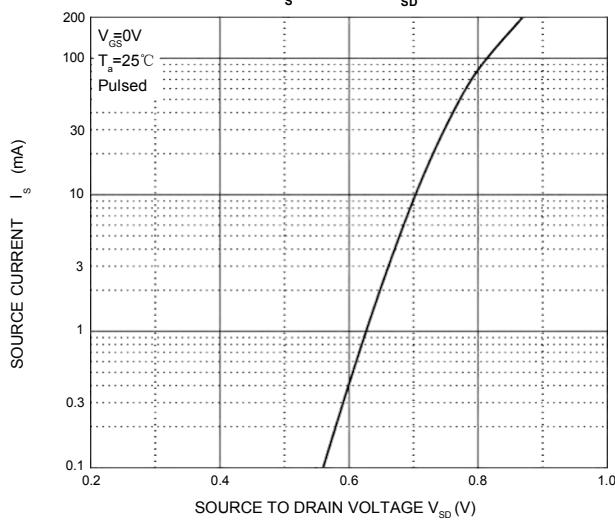
$R_{DS(ON)}$  ——  $I_D$



$R_{DS(ON)}$  ——  $V_{GS}$



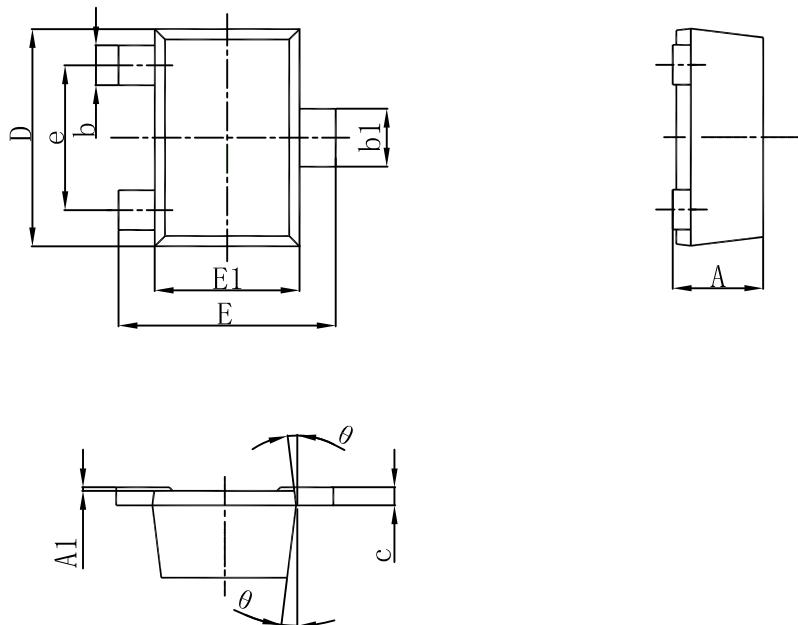
$I_s$  ——  $V_{SD}$





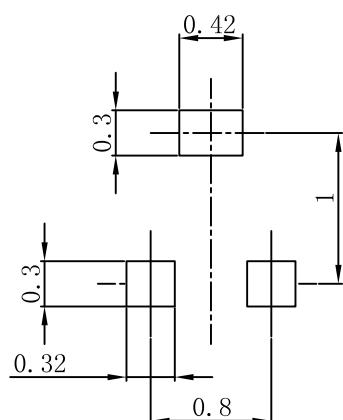
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### SOT-723 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.450	0.550	0.018	0.022
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

### SOT-723 Suggested Pad Layout



#### Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$ mm.
3. The pad layout is for reference purposes only.